

Silicon-Based Technology Corp.

Small-Signal Schottky Barrier Diodes

SBT101W Series

SBT101W series are Schottky Barrier Diodes fabricated by a series of proprietary Schottky barrier patents and technologies (SBT[®]) developed by Silicon-Based Technology Corporation, which exhibit high-performance characteristics for modern switching, conversion and protection applications with high speed and low power consumptions. The package types as described in this data sheet are set forth in routine production; other packages are available upon special orders.

■ Features and Advantages:

- Low forward voltage drop (V_F)
- Low reverse leakage current (I_R)
- Very small conduction power loss
- Very small switching power loss
- Very high switching speed
- Very high reliability

■ Electrical Characteristics : (@ $T_A=25^\circ\text{C}$ unless otherwise specified)

Characteristic		Symbol	Min.	Max.	Unit	Test Conditions
Reverse Breakdown Voltage	SBT101AW SBT101BW SBT101CW	$V_{(BR)R}$	60 50 40	-	V	$I_R=10\mu\text{A}$
Forward Voltage Drop	SBT101AW SBT101BW SBT101CW SBT101AW SBT101BW SBT101CW	V_F	-	0.30 0.30 0.28 0.60 0.60 0.55	V	$I_F=1.0\text{mA}$ $I_F=1.0\text{mA}$ $I_F=1.0\text{mA}$ $I_F=15\text{mA}$ $I_F=15\text{mA}$ $I_F=15\text{mA}$
Peak Reverse Current (Note 2)	SBT101AW SBT101BW SBT101CW	I_{RM}	-	200	nA	$V_R=50\text{V}$ $V_R=40\text{V}$ $V_R=30\text{V}$
Total Capacitance	SBT101AW SBT101BW SBT101CW	C_T	-	2.0 2.1 2.2	pF	$V_R=0\text{V}$, $f=1.0\text{MHz}$
Reverse Recovery Time		t_{rr}	-	1.0	ns	$I_F=I_R=5.0\text{mA}$, $I_{rr}=0.1 \times I_R$, $R_L=100\Omega$



Silicon-Based Technology Corporation

1F, No. 23, R&D Rd. I, Hsinchu Science Park, Taiwan, R.O.C

Tel : 886-3-5777897

Fax : 886-3-5779832

**■ Maximum Ratings : (@T_A=25°C unless otherwise specified)**

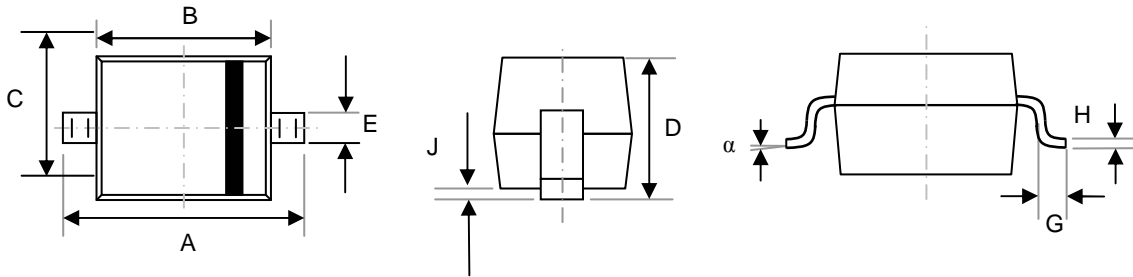
Characteristic	Symbol	SBT101AW	SBT101BW	SBT101CW	Unit
Peak Repetitive Reverse Voltage	V _{RRM}				
Working Peak Reverse Voltage	V _{RWM}	60	50	40	V
DC Blocking Voltage	V _R				
RMS Reverse Voltage	V _{R(RMS)}	42	35	28	V
Forward Continuous Current (Note 1)	I _{FM}	15			mA
Non-Repetitive Peak @t≤1.0s	I _{FSM}	50			mA
Forward Surge Current @t=10μs		2.0			A
Power Dissipation (Note 1)	P _d	400			mW
Thermal Resistance, Junction to Ambient Air (Note 1)	R _{θJA}	300			°C/W
Operating and Storage Temperature Range	T _j , T _{STG}	-65 to +125			°C

- Notes: 1. Part mounted on FR-4 PC board with a recommended pad layout, which can be found on our website at www.sbt.com.tw
2. Short duration test pulse is used to minimize self-heating effect.

■ Package Data :

- Case: Molded Plastic Material (UL Flammability Classification 94V-0)
- Terminals: Solderable Plated Terminals (MIL-STD-202, Method 208)
- Lead Free Plating (Matte Tin Finish)
- Polarity: See device configurations below
- Approx. Weight: 0.01 grams.
- Package outline and dimensions (see below)

SOD-123



DIMENSIONS (MM)										
	A	B	C	D	E		G	H	J	α
Min.	3.55	2.55	1.40	-	0.45	0.55	0.25	0.11	-	0°
Max.	3.85	2.85	1.70	1.35	0.65	Typical	-	Typical	0.10	8°

■ Ordering Information (Note 3)

Part Number	Marking Code	Packaging Type	Shipping
			7" Tape & Real
SBT101AW	SBTJAW	SOD-123	3K
SBT101BW	SBTJBW	SOD-123	3K
SBT101CW	SBTJCW	SOD-123	3K

Notes: 3. Website at <http://www.sbt.com.tw>

4. Bulk package in a box form is also available upon request.

5. Day code marking is YM, in which Y represents year (For example: 2005 is marked by 5);

M represents month in a year (For example: March is marked by C; November is marked by K).